Appl. No.: 10/677,643
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Amendments to the Specification:

Please replace paragraph [0045] with the following amended paragraph:

"In one embodiment the substrate comprises a single crystalline material, such as a *p* or *n* doped single crystalline wafer, or a substrate of SOI (Silicon-On Insulator). For example, a (110) silicon wafer can be used as a substrate, which makes it possible to use crystallographic dependant etching for the minimization of the n-hill sidewall roughness. The flat and smooth sidewalls can be obtained, corresponding to the (111) crystal planes, that are perpendicular to the surface in (110) wafers. Accordingly, this embodiment beneficially offers decreased sidewall roughness and further offers etch protection of the sidewall."

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